

# Ian C Sandall

## List of Publications by Year in descending order

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37  
papers

426  
citations

759055

12  
h-index

752573

20  
g-index

39  
all docs

39  
docs citations

39  
times ranked

386  
citing authors

#	ARTICLE	IF	CITATIONS
1	InAs Diodes Fabricated Using Be Ion Implantation. IEEE Transactions on Electron Devices, 2015, 62, 2928-2932.	1.6	60
2	The effect of p doping in InAs quantum dot lasers. Applied Physics Letters, 2006, 88, 111113.	1.5	52
3	Temperature dependence of threshold current in p-doped quantum dot lasers. Applied Physics Letters, 2006, 89, 151118.	1.5	44
4	Gain in p-doped quantum dot lasers. Journal of Applied Physics, 2007, 101, 013107.	1.1	34
5	Temperature-Dependent Gain and Threshold in P-Doped Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2007, 13, 1261-1266.	1.9	33
6	1300 nm Wavelength InAs Quantum Dot Photodetector Grown on Silicon. Optics Express, 2012, 20, 10446.	1.7	31
7	The role of high growth temperature GaAs spacer layers in 1.3- $\mu\text{m}$ In(Ga)As quantum-dot lasers. IEEE Photonics Technology Letters, 2005, 17, 2011-2013.	1.3	20
8	Origin of Temperature-Dependent Threshold Current in p-Doped and Undoped In(Ga)As Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1162-1170.	1.9	19
9	Recombination mechanisms in 1.3- $\mu\text{m}$ InAs quantum-dot lasers. IEEE Photonics Technology Letters, 2006, 18, 965-967.	1.3	16
10	Measurement of modal absorption, gain and recombination in p-doped and intrinsic quantum dot structures. IEE Proceedings: Optoelectronics, 2006, 153, 316-320.	0.8	15
11	Linear array of InAs APDs operating at 2 $\mu\text{m}$ . Optics Express, 2013, 21, 25780.	1.7	15
12	Temperature dependence of impact ionization in InAs. Optics Express, 2013, 21, 8630.	1.7	14
13	Localized Auger Recombination in Quantum-Dot Lasers. IEEE Journal of Quantum Electronics, 2007, 43, 1140-1146.	1.0	12
14	Improved performance of 1.3- $\mu\text{m}$ In(Ga)As quantum-dot lasers by modifying the temperature profile of the GaAs spacer layers. IEEE Photonics Technology Letters, 2006, 18, 1557-1559.	1.3	8
15	High-Gain InAs Planar Avalanche Photodiodes. Journal of Lightwave Technology, 2016, 34, 2639-2644.	2.7	8
16	Nonradiative Recombination in Multiple Layer In(Ga)As Quantum-Dot Lasers. IEEE Journal of Quantum Electronics, 2007, 43, 698-703.	1.0	7
17	X-shaped plasmonic antenna on a quantum cascade laser. Applied Physics Letters, 2010, 96, 151105.	1.5	6
18	AlGaInP laser diodes incorporating a $3\lambda/4$ multiple quantum barrier. Applied Physics Letters, 2005, 86, 021102.	1.5	5

#	ARTICLE	IF	CITATIONS
19	Influence of annealing on the electrical characteristic of GaSbBi Schottky diodes. Journal of Applied Physics, 2019, 126, .	1.1	5
20	Planar InAs photodiodes fabricated using He ion implantation. Optics Express, 2012, 20, 8575.	1.7	4
21	Terahertz optical sideband emission in self-assembled quantum dots. Applied Physics Letters, 2010, 96, .	1.5	3
22	High temperature and wavelength dependence of avalanche gain of AlAsSb avalanche photodiodes. Optics Letters, 2011, 36, 4287.	1.7	3
23	Growth and characterization of multiple layer quantum dot lasers. , 2005, , .		2
24	Maximising the gain: optimising the carrier distribution in InGaAs quantum dot lasers. , 2007, , .		2
25	Planar InAs photodiodes fabricated using He ion implantation. , 2012, , .		2
26	Suppression of Surface Leakage Currents in InAs Avalanche Photodiodes via Sputtering of High- <i>k</i> Dielectric Layers. IEEE Transactions on Electron Devices, 2020, 67, 4269-4273.	1.6	2
27	Recombination in quantum dot ensembles. , 2007, , .		1
28	Planar InAs p-i-n photodiodes fabricated using ion implantation. , 2014, , .		1
29	Characterisation of modulation doped quantum dot lasers. , 2006, , .		0
30	Localised recombination in quantum dot structures. , 2006, , .		0
31	InAsBi photodiode operating in the MWIR. , 2014, , .		0
32	InAs APD with solid state photomultiplier characteristics. , 2014, , .		0
33	Temperature dependence of impact ionization in InAs: erratum. Optics Express, 2014, 22, 25923.	1.7	0
34	Demonstration of an InAsBi photodiode operating in the MWIR. Proceedings of SPIE, 2014, , .	0.8	0
35	Planar InAs avalanche photodiodes. , 2015, , .		0
36	InAs-QDIP hybrid broadband infrared photodetector. MRS Advances, 2016, 1, 3301-3306.	0.5	0

#	ARTICLE	IF	CITATIONS
37	GaSbBi Metal Semiconductor Metal Detectors for Mid-Infrared Sensing. Frontiers in Electronic Materials, 0, 2, .	1.6	0